

Amendments To The Specification:

Please amend paragraph [Para 7] on page 2, wherein strikethrough and double brackets indicates a deletion and underlining indicates additions, as follows:

FIG. 2 is a circuit block diagram showing a prior art driving circuit of DRAM. The operation of the DRAM 20 is similar to that described above. However, there is a disadvantage in the prior art DRAM. In order to provide the voltage VPP, which is higher than the normal power voltage, a charge pump 200 is applied in the driving circuit of the DRAM shown in FIG. 2. Since the bit line BL and the bit line bar BLB have to be charged to one half of the power voltage VDD, DRAM 20 has to supply direct ~~current~~ voltage of VDD/2. Because of the charge pump 200 and the additional direct ~~current~~ voltage, the DRAM 20 consumes powers even when it is in stand-by mode. The power consumption shortens the service life of cells of portable devices.

Please amend paragraph [Para 11] on page 3 , wherein strikethrough and double brackets indicates a deletion and underlining indicates additions, as follows:

According to an embodiment of the present invention, the method is adapted to the DRAM using a [[word]] bit line and a [[word]] bit line bar, and a charge storage device is adapted for storing data. The charge storage device is coupled to the [[word]] bit line via a switch device. When the switch device is turned on, a switch voltage drop is generated between the two ends of the switch. The charge storage device is programmed with a first voltage, which is VDD minuses the switch voltage, or a zero voltage. The method can also access the data. For accessing the data, the [[word]] bit line and [[word]] bit line bar are charged to the power voltage. Next, the switch device is turned on and then the data stored in the charge storage device is determined according to a voltage difference between bit line and bit line bar.